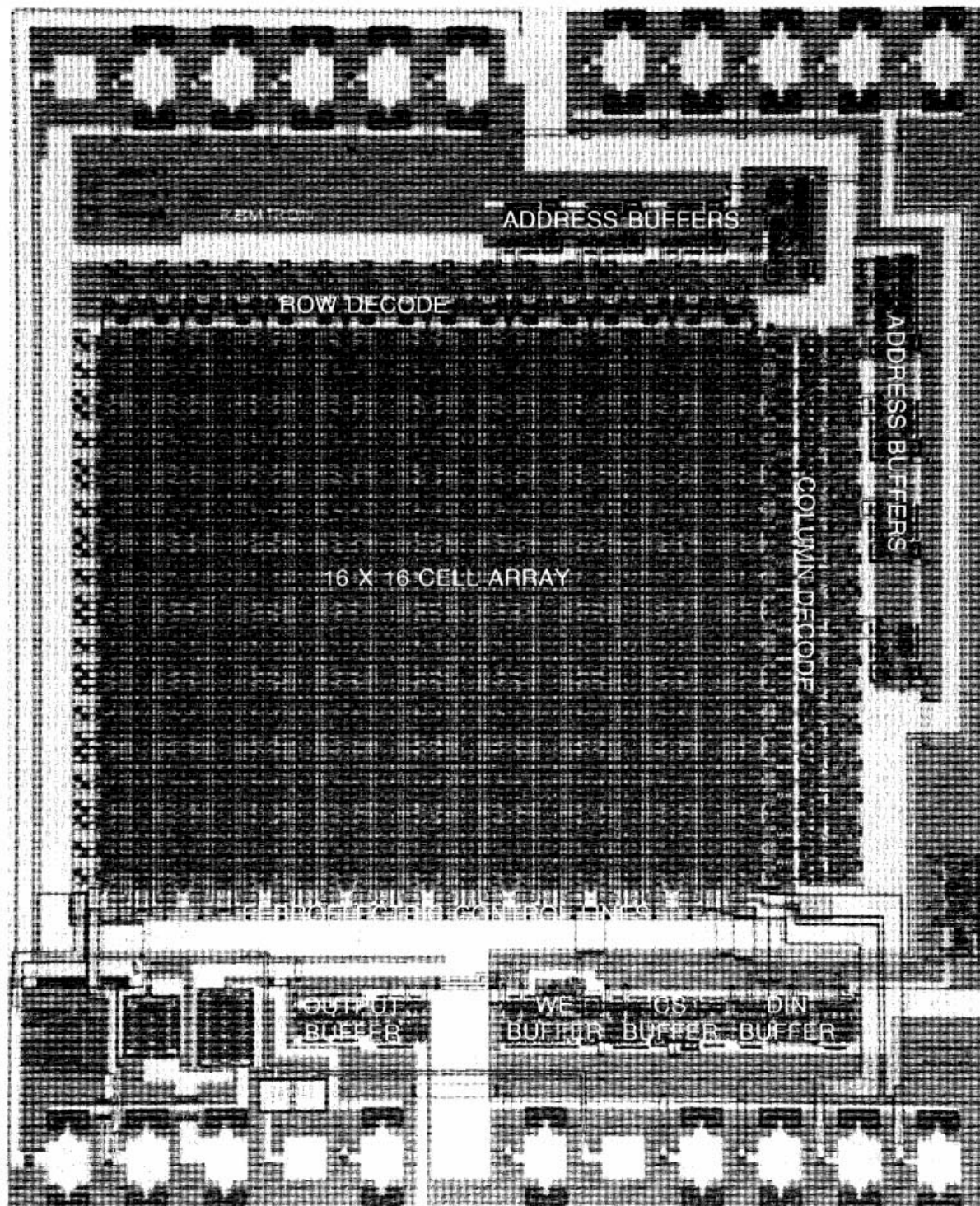


# FIRST FERROELECTRIC NONVOLATILE MEMORY

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## A Ferroelectric Nonvolatile Memory

EATON ET AL. (Ramtron Corporation) presented the first 256-bit ferroelectric memory using thin film PZT (lead zirconate titante) capacitors. These nonlinear PZT capacitors were used for nonvolatile shadow store and re-store of static RAM cells. Using 4  $\mu\text{m}$  design rules, the 256 bit memory was 4.0 mm x 3.2 mm. This work ushered in the development of many different types of ferroelectric memories that are in use today.

S.S. Eaton    D.B. Butler    M. Parris    D. Wilson    H. McNeillie  
Ramtron Corp., Colorado Springs, CO